The new variable resolution Associative Memory for Fast Track finding aka AMchip04

WIT May 3-5, 2012, Pisa

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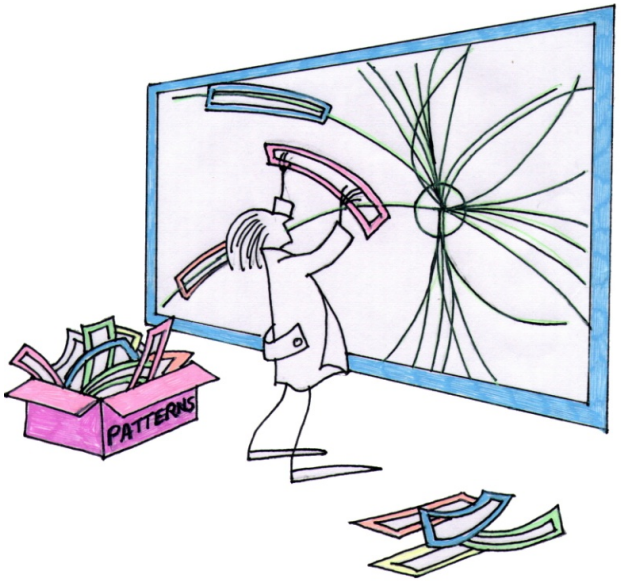
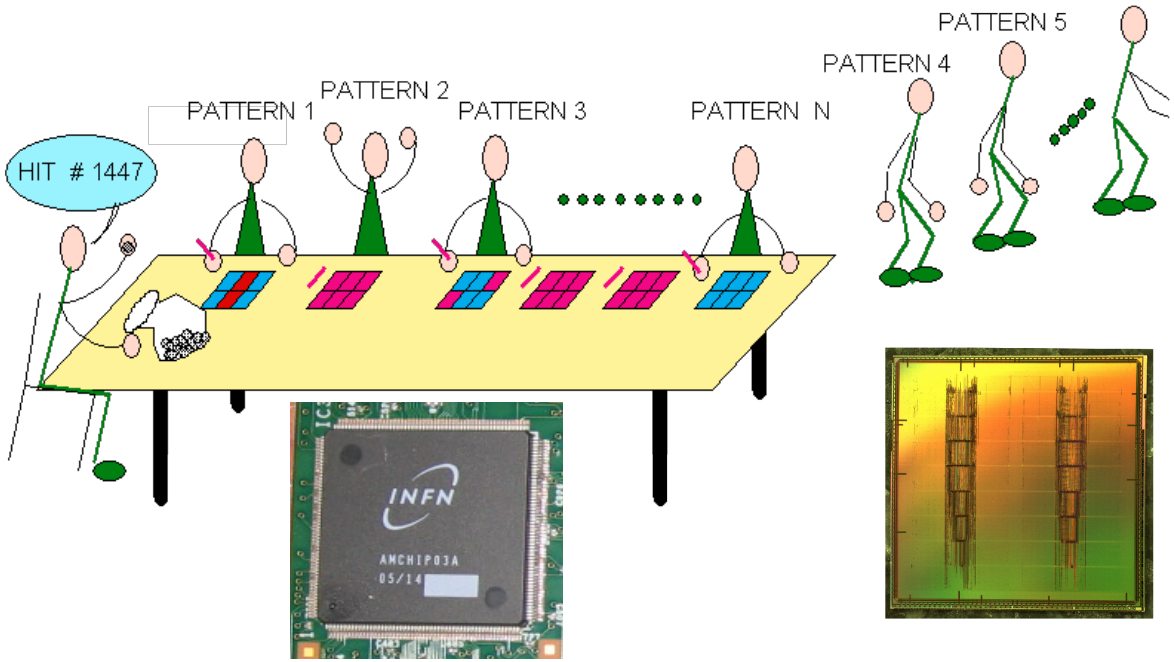
FTK algorithm:
Pattern recognition & Track fitting

See Thu B. Penning's talk

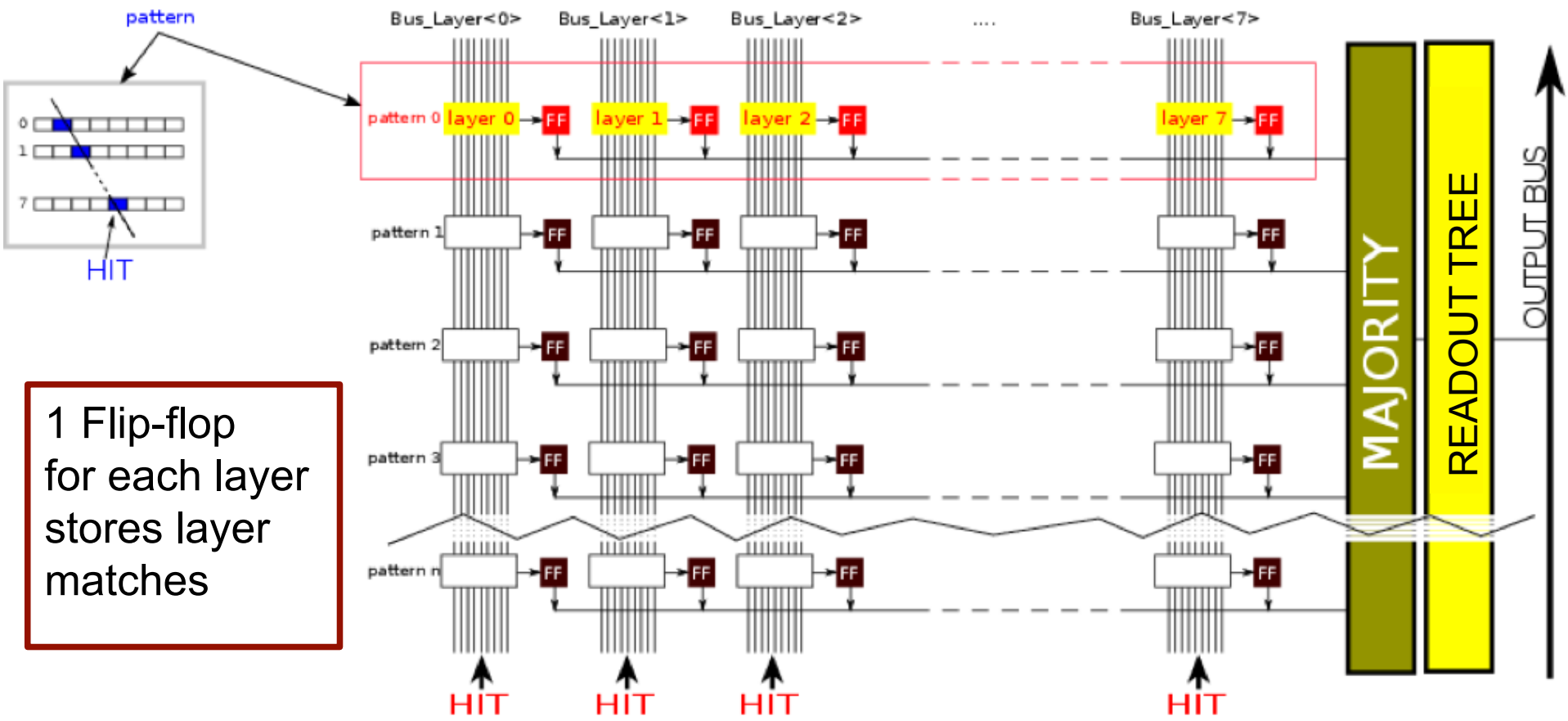
- Pattern recognition – find track candidates with enough Si hits





  - O(10^9) prestored patterns simultaneously see the silicon hits leaving the detector at full speed.
  - Based on the Associative Memory chip (content-addressable memory) initially developed for the CDF Silicon Vertex Trigger (SVT).

AM working principle



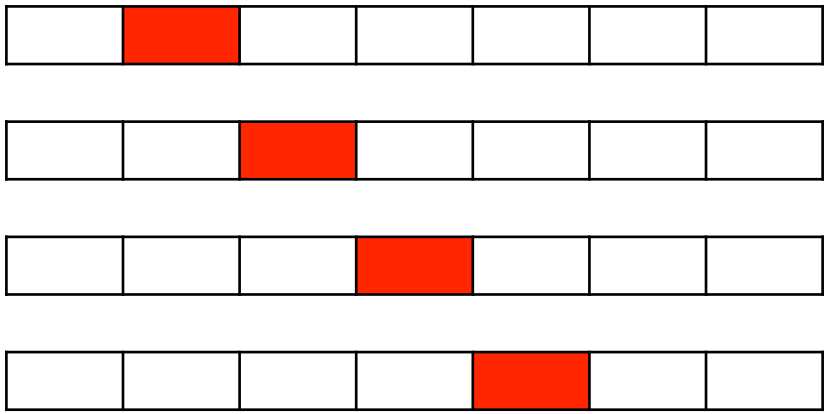
1 Flip-flop for each layer stores layer matches

All patterns compared in parallel with incoming data. Look for correlation of data received at different times. (Feature unique to AMchip)

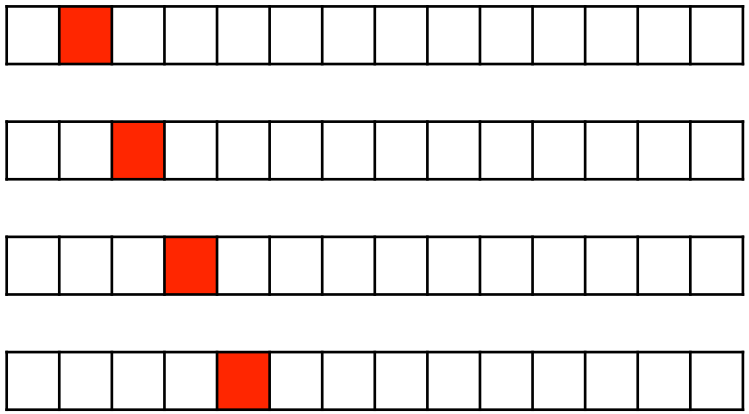
Fast pattern matching. Flexible input: position, time, objects…

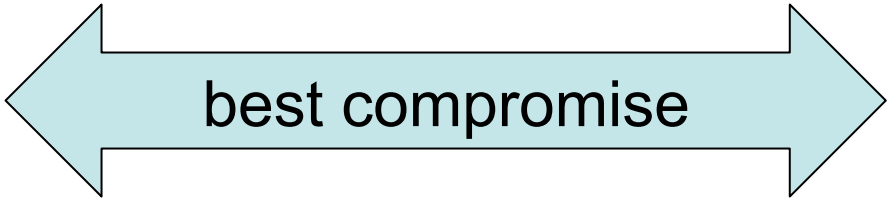
Generatig the pattern bank

Wide patterns



Thin patterns





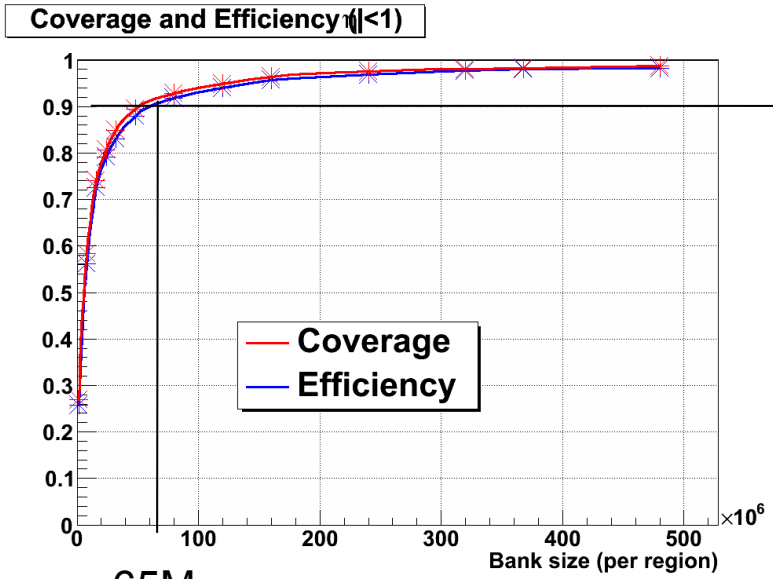
High efficiency
with less patterns (hardware)
BUT more fakes

More patterns (hardware)
for same efficiency
less fakes

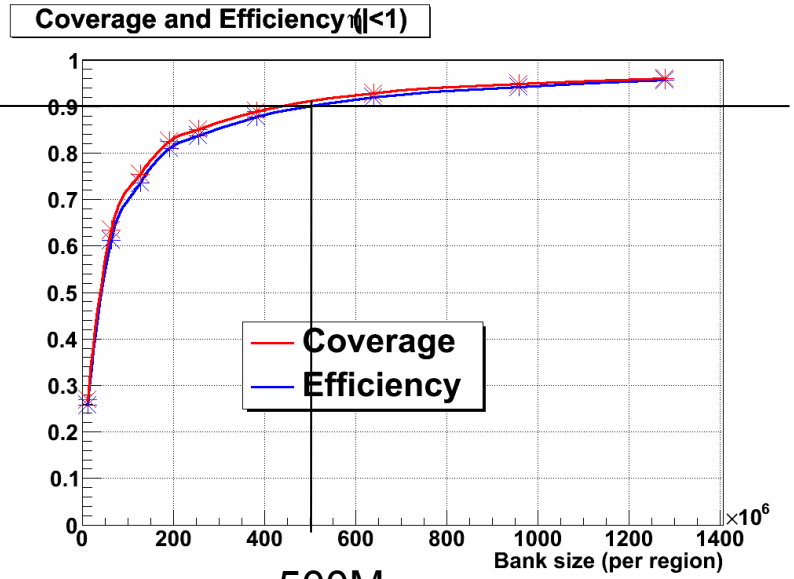
Pattern efficiency

Pattern size
r-ϕ: 24 pixels, 20 SCT strips
z: 36 pixels

Pattern size (half size)
r-ϕ: 12 pixels, 10 SCT strips
z: 36 pixels



65M



90%

500M

# of patterns in Amchips (barrel only, 45 ϕ degress)

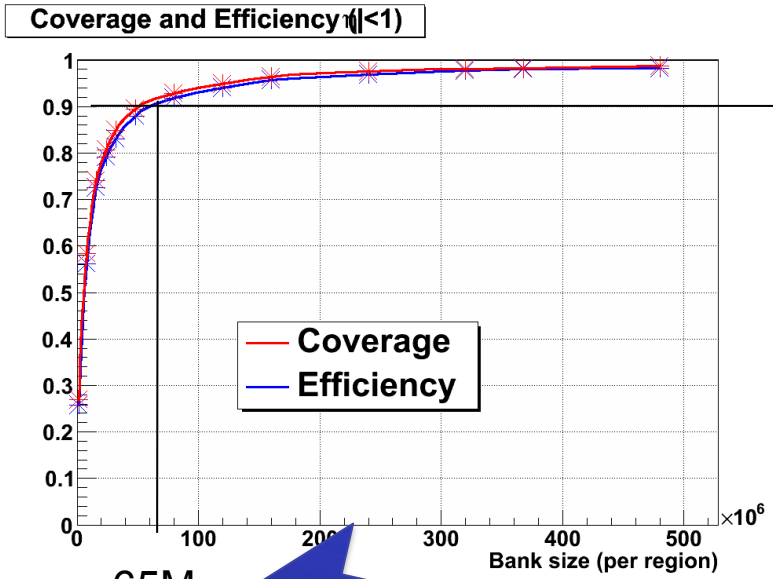
<# matched patters/event @ 3E34> = 342k

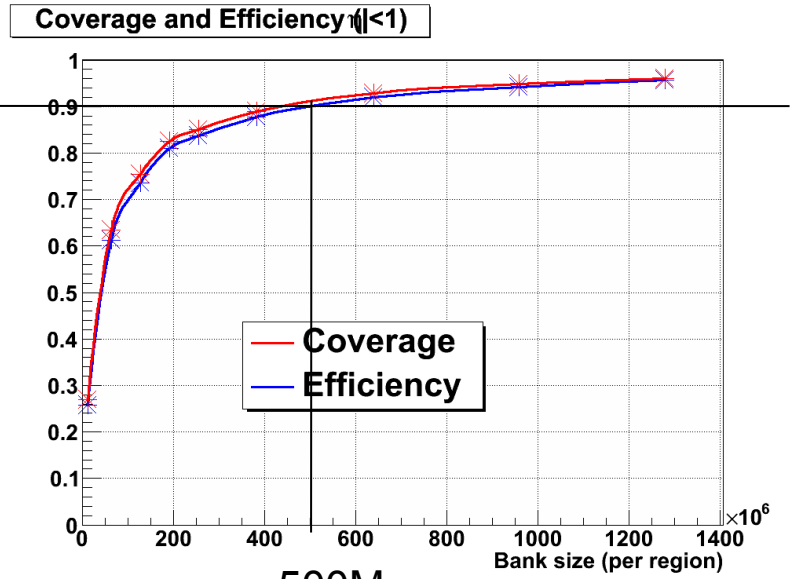
<# matched patters/event @ 3E34> = 40k

Pattern efficiency

Pattern size
r-ϕ: 24 pixels, 20 SCT strips
z: 36 pixels

Pattern size (half size)
r-ϕ: 12 pixels, 10 SCT strips
z: 36 pixels





90%

65M

500M

o (barrel only, 45 ϕ degress)

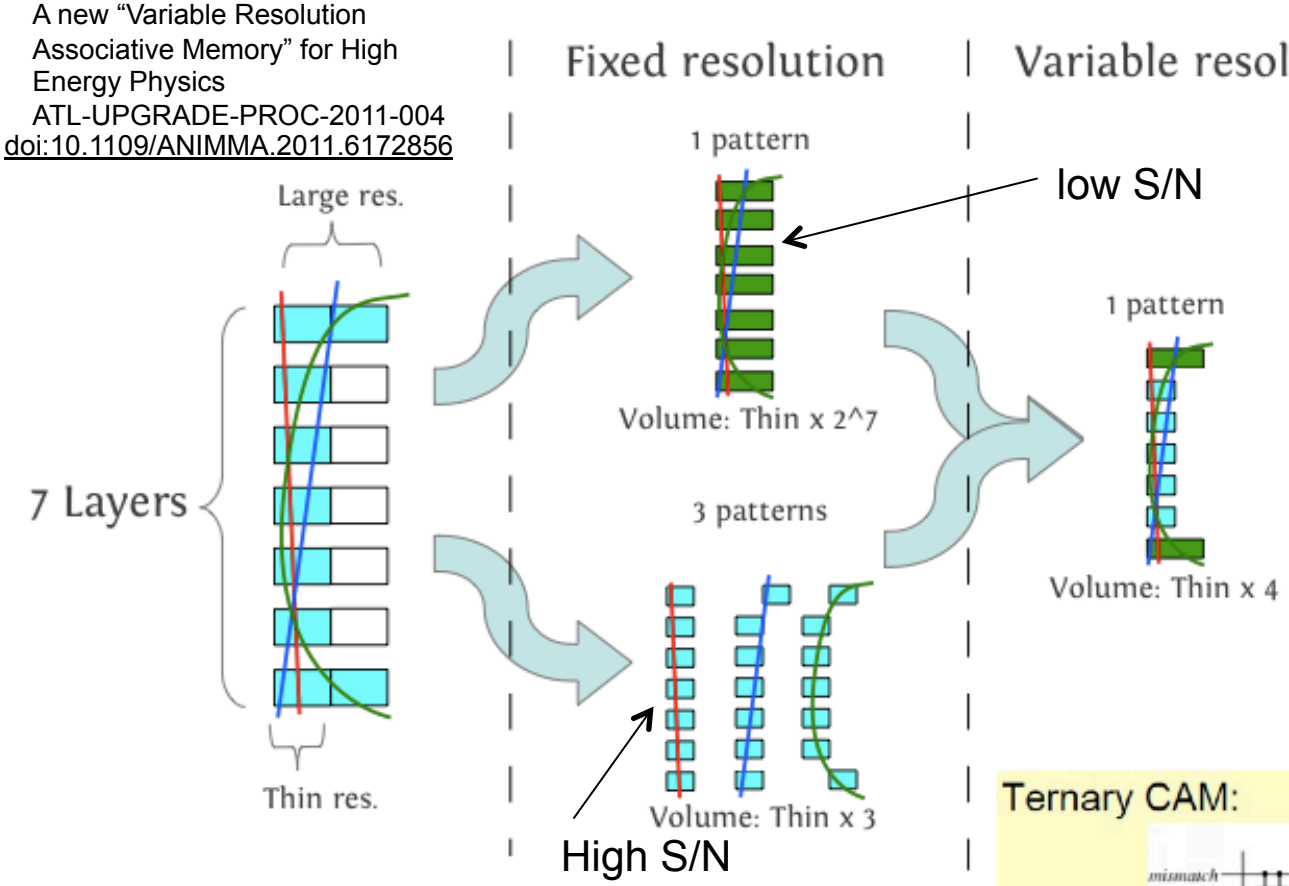
Want this

<# matched patters/event @ 3E34> = 342k

atched patters/event @ 3E34> = 40k

AMCHIP04: VARIABLE RESOLUTION

A new "Variable Resolution Associative Memory" for High Energy Physics
ATL-UPGRADE-PROC-2011-004
doi:10.1109/ANIMMA.2011.6172856

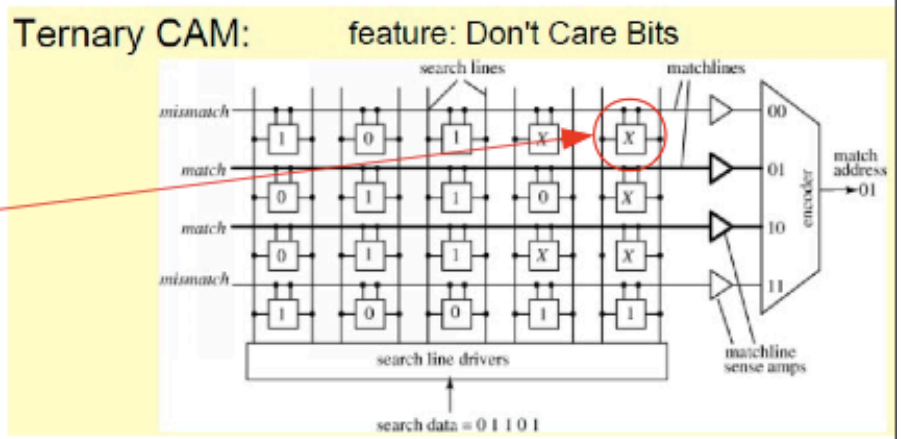


Good rejection and occupy only one pattern location.

Per-pattern choice of optimal resolution.

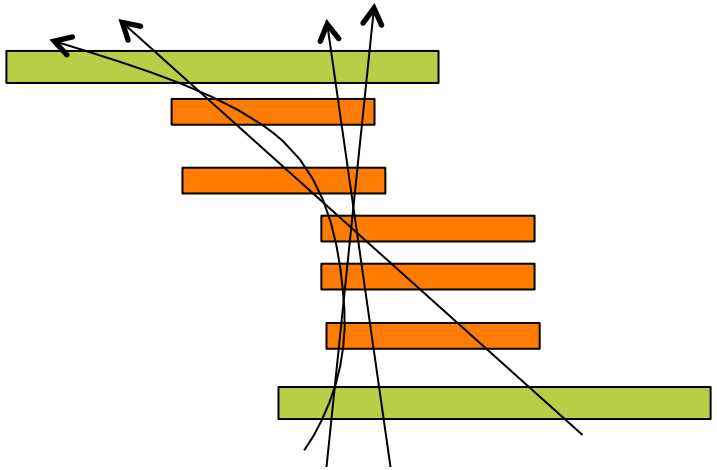
We can use **don't care** on the least significant bit when we want to match the **pattern layer @ Large resolution** or use all the bits to match it **@ Thin resolution**

Coincidence window is programmable layer by layer and pattern by pattern

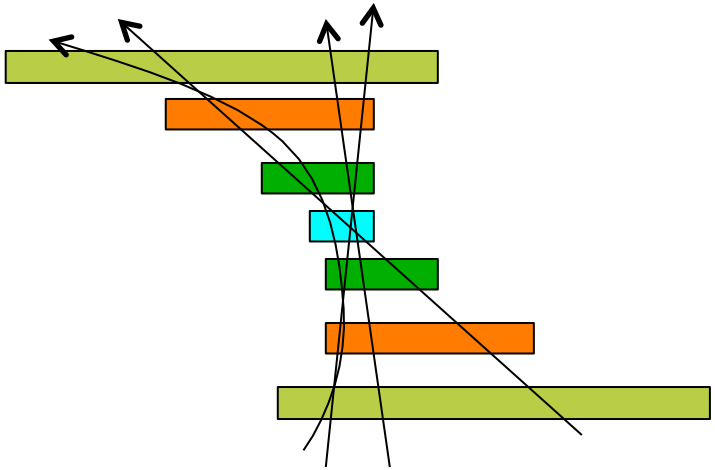


Many bits variable resolution

1 bit variable resolution



3 bit variable resolution



1 pattern
Volume 4*
Volume 2^(7*2)*4* = 2^16

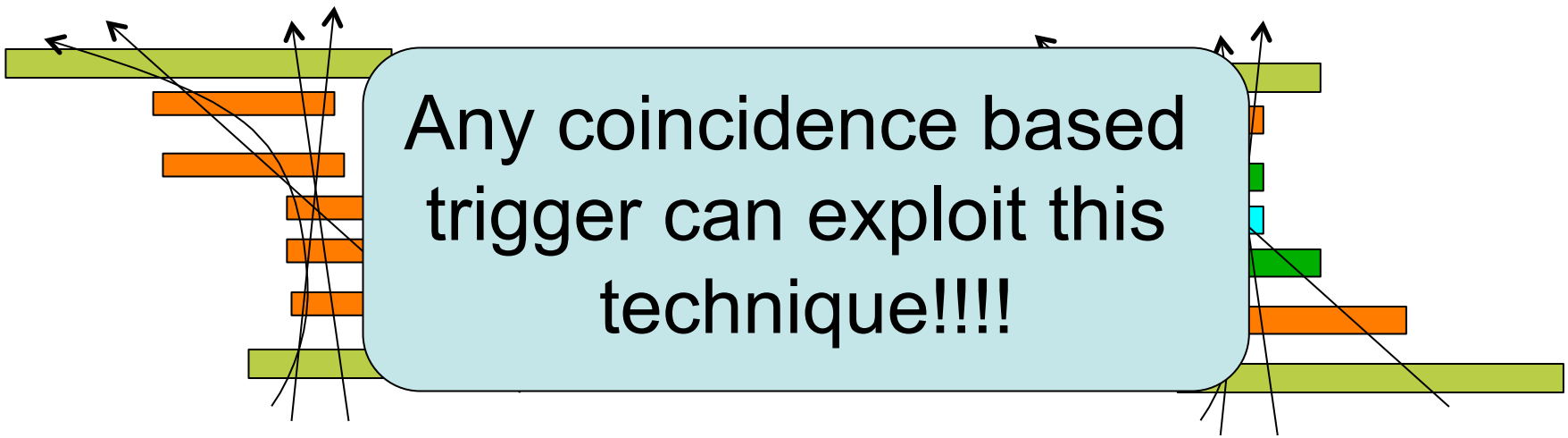
1/16 less volume
1/16 less fakes!!!

1 pattern
Volume 1/4*
Volume 2^12

Many bits variable resolution

1 bit variable resolution

3 bit variable resolution



Any coincidence based trigger can exploit this technique!!!!

1 pattern
Volume 4*
Volume 2^(7*2)*4* = 2^16

1/16 less volume
1/16 less fakes!!!

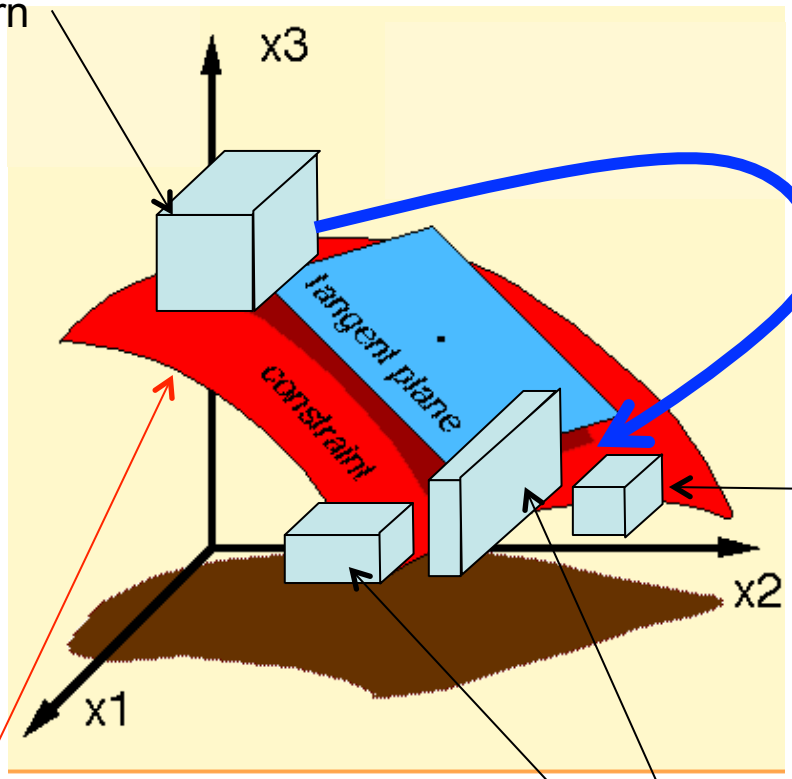
1 pattern
Volume 1/4*
Volume 2^12

The patterns: a different point of view

5 strip + 3 pixel layers
→11 coordinates
→11D hit coord. space

Large pattern

The pattern bank:
• cover the track manifold with patterns.
• covered space outside manifold → fakes.
• variable resolution → dramatically improves S/N



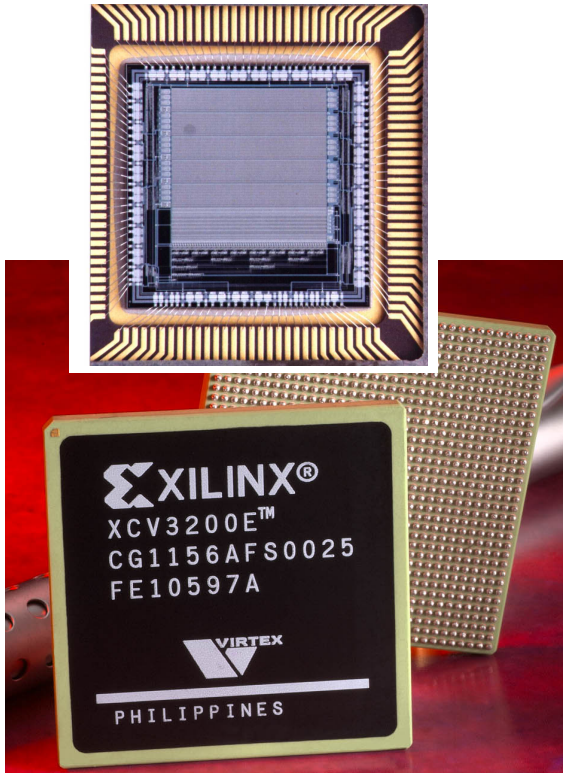
A factor of 2 on each side
→a factor 2^11 less volume
→O(1/2048) less fakes!!

Thin pattern

5D track manifold

Variable resolution patterns

AM chips from 1992 to 2005



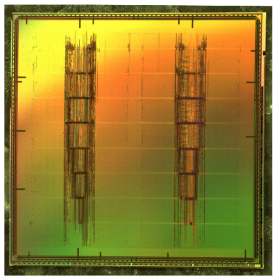
- (90's) **Full custom VLSI chip -** 0.7μm (INFN-Pisa)
- **128 patterns, 6x12bit words each**
- **384k patterns (SVT total)**

F. Morsani et al., "The AMchip: a Full-custom MOS VLSI Associative memory for Pattern Recognition", IEEE Trans. on Nucl. Sci., vol. 39, pp. 795-797, **(1992).**

On the opposite side: **FPGA** for the same AMchip

P. Giannetti et al. "A Programmable Associative Memory for Track Finding", Nucl. Intsr. and Meth., vol. A413/2-3, pp. 367-373, **(1998).**

G Magazzu' I progetto standard cell presented @ LHCC (1999)



In the middle: **Standard Cell 0.18** μm (INFN-Pisa-Ferrara)→ 5000 pattern/chip Amchip SVT upgrade total: 6M patterns

L. Sartori, A. Annovi et al., "A VLSI Processor for Fast Track Finding Based on Content Addressable Memories", **IEEE Transactions on Nuclear Science**, Volume 53, Issue 4, Part 2, Aug. **2006** Page(s):2428 - 2433

AMchip03 array (AM board)

See the FTK processing unit poster

AMchip Comparison

	AMchip03	AMchip04	Effect
Technology	180nm	65nm	x8 pattern density
Clock freq.	50MHz	100MHz	faster, higher power cons.
Die size	10x10mm^2	12x12mm^2	x1.5 patterns prototype 3.5x4 mm^2
Core voltage	1.8V	1.2V	lower power consumption
Core power	1.3W	2W	at 40MHz and 100MHz respectively
Selec. Prech.	No	Yes	~80% power saving
Full custom	No	Yes	x2 pattern density
Layers	6 (or 12)	8	¾ pattern density
Patters/chip	5k	80k	8k in AMchip04 prototype
Bits/layer	up to 18	up to 15	
Ternary/layer	N/A	3 to 6	better S/N with variable resolution
		2 event "buffers": readout 1st, load 2nd event	

The hard part: FTK goal 1 billion pattern for LHC phase I

push pattern density to the limit, keep power under control despite x16 patterns x8/6 layers and 40MHz --> 100MHz

would mean x50 power consumption with same design & technology

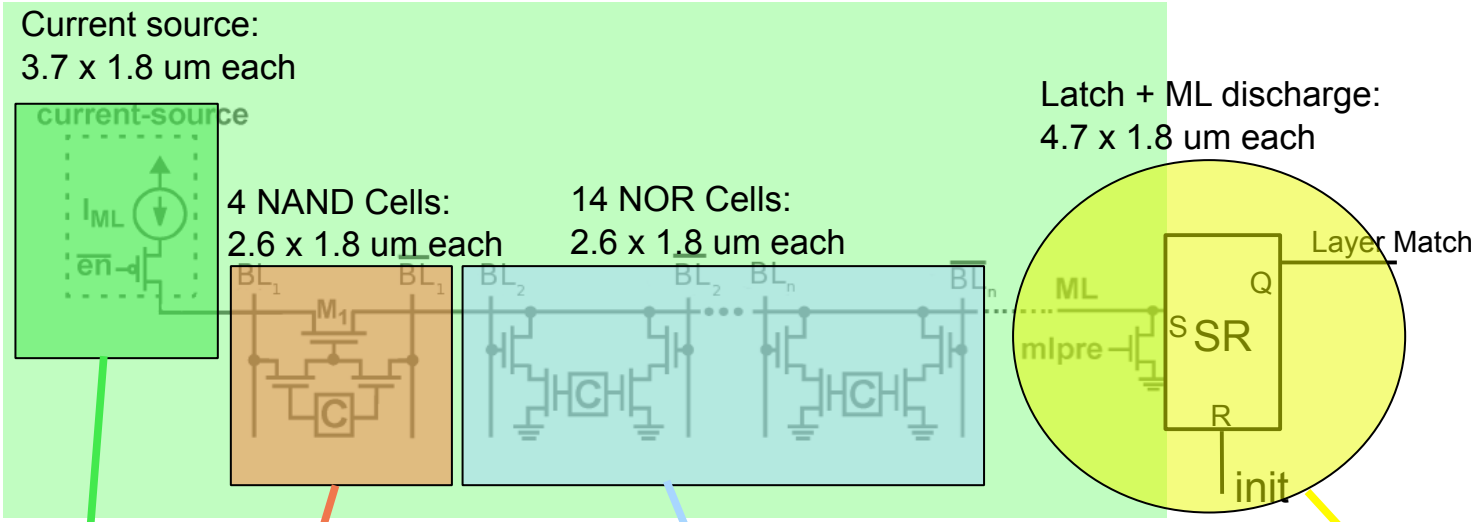
AM chip04 functions / specs

- Store pre-calculated trajectories (patterns)
  - Each pattern: 8 positions (numbers or words) one for each layer
- Compare patterns with incoming data
  - Detectors hits for one event
- For each event readout patterns
  - with enough hits 8/8, 7/8 or 6/8
- For each pattern readout:
  - Pattern address (ID) + bitmap of fired layers
- Configuration and pattern loading through JTAG interface

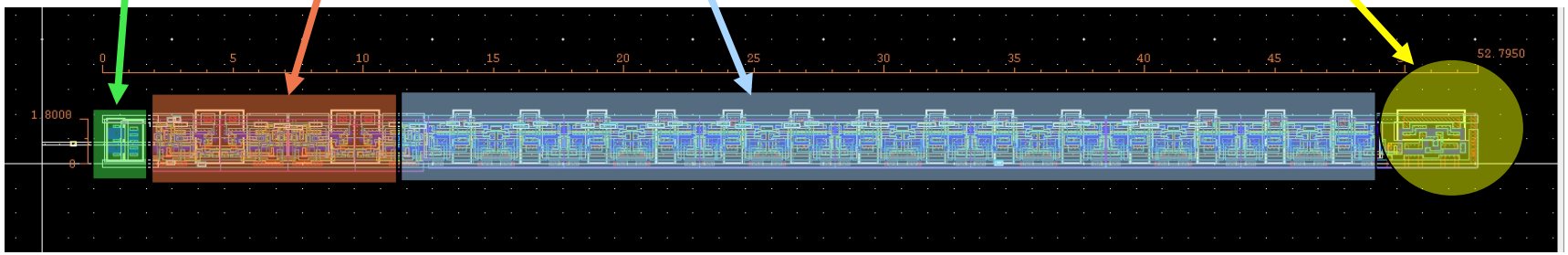
Associative Memory Layer

To save power we have used two different match line driving scheme:

- *Current race scheme (dummy layer timing)*
- *Selective precharge scheme*



Full Layer layout : w=~53µm X h=1.8 µm



Current race and selective - precharge schemes

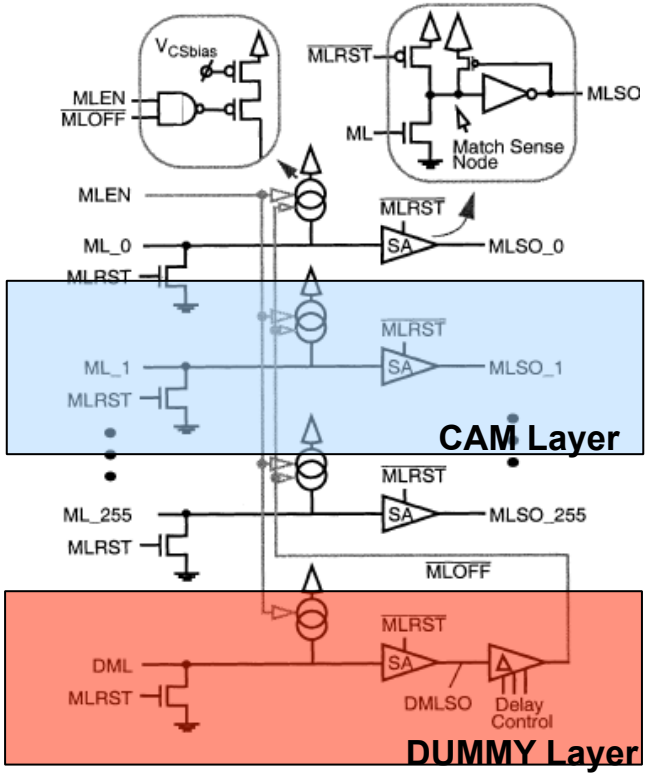


Fig. 5. Current-race ML sensing scheme.

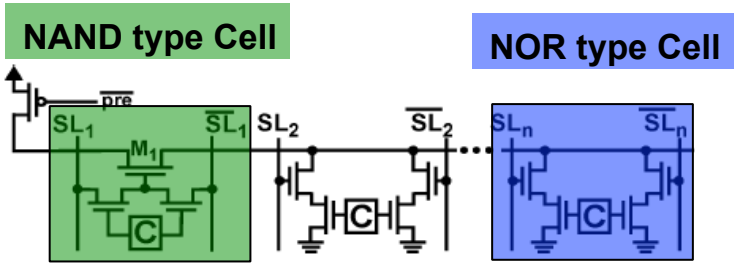


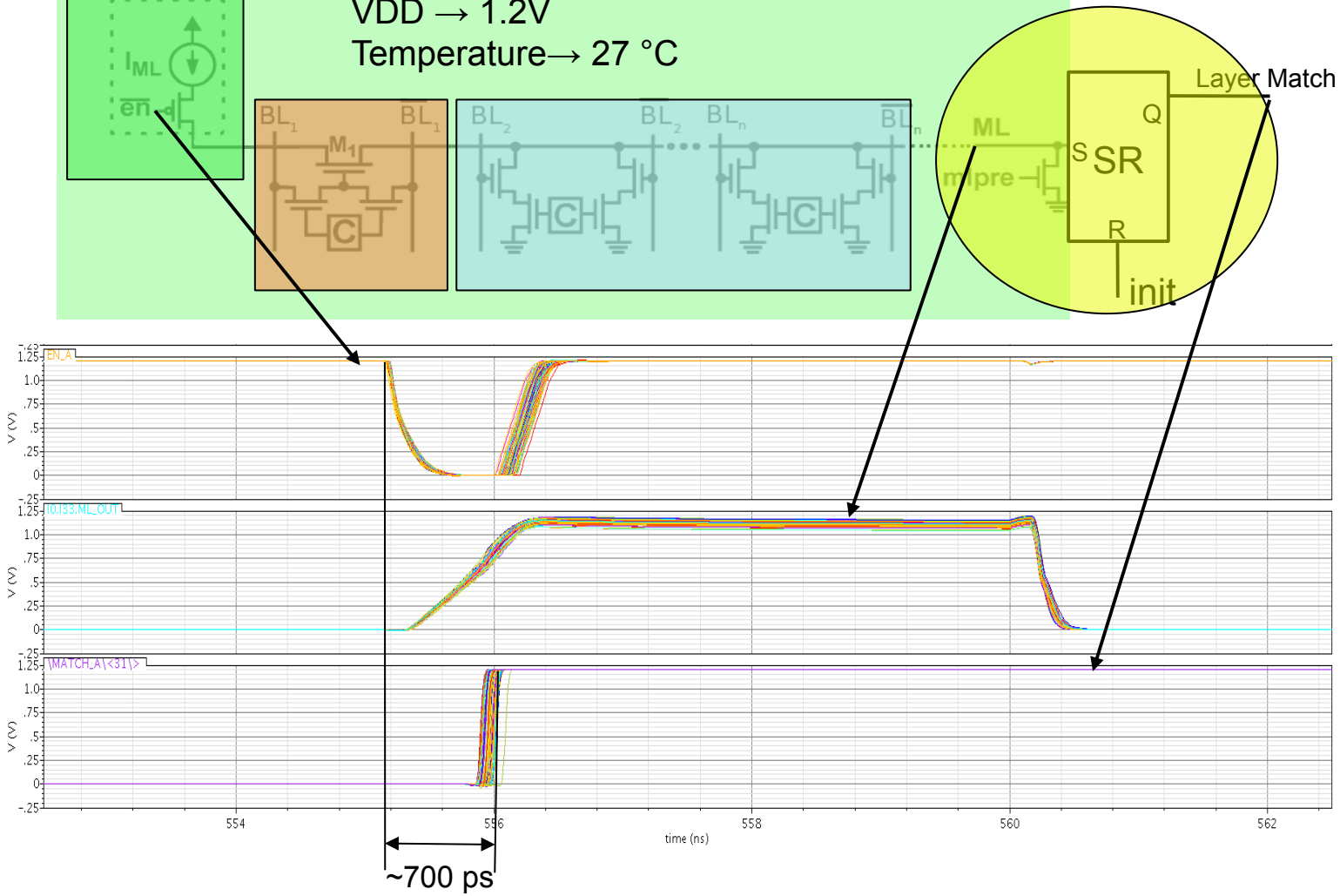
Fig. 16. Sample implementation of the selective-precharge matchline technique [43]. The first cell on the matchline is a NAND cell, while the other cells are NOR cells. Precharge occurs only in the case where there is a match in the first cell. If there is no match in the first cell, the precharge transistor is disconnected from the matchline, thus saving power.

Scheme from: "*Content-Addressable Memory (CAM) Circuits and Architectures: A Tutorial and Survey*", Kostas Pagiamtzis and Ali Sheikholeslami IEEE Journal of Solid-State Circuits, Vol. 41, NO. 3, March 2006

Scheme from: "*A ternary content-addressable memory (TCAM) based on 4T static storage and including a Current-Race sensing scheme*", Ali Sheikholeslamiet Al. IEEE Journal of Solid-State Circuits, Vol. 38, NO. 1, January 2003

CAM layer timing diagram

Simulation done in nominal conditions:
Transistors models → TT
VDD → 1.2V
Temperature→ 27 °C



Power consumption rough estimates

To be verified with prototype measurement

We use the nominal simulation condition:
Transistor models : Typical
Power supply : 1.2 V
Temperature : 27 °C
Frequency :100 MHz

These values do not take into account the standard cells part of the chip and the on chip power supply network distribution parasitic and other parasitic.

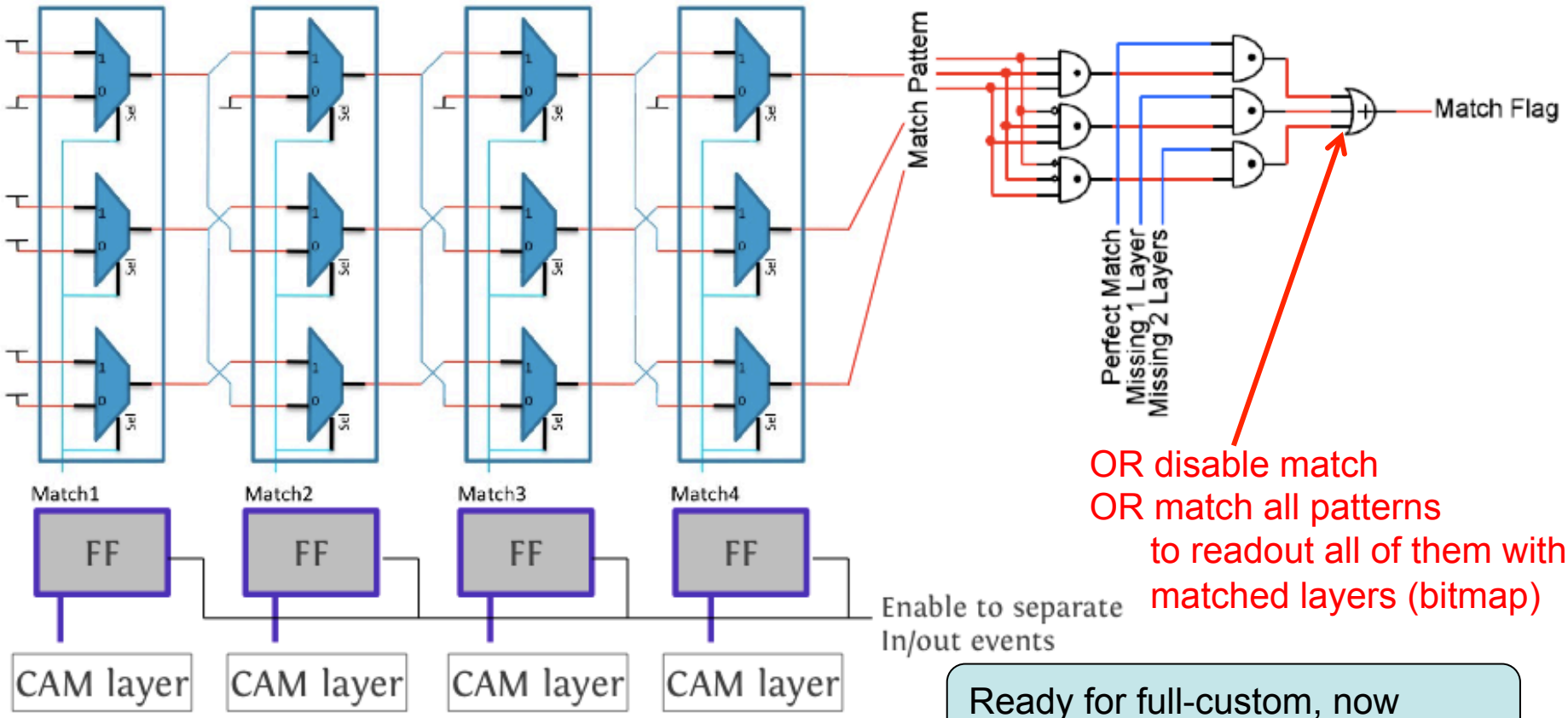
Memory state	Mean (mW)	Max (mW)	RMS (mW)
Write	23.04	557.57	28.12
Quiescent	21.89	22.09	21.88
Don't match	63.36	720.32	113.41
Match 1 out of 16 patterns	70.96	814.18	123.55
Match 1 out of 8 patterns	79.20	868.03	140.03
Match 1 out of 4 patterns	91.87	1045.44	172.34

Appoximate consumption 80mW / 8kpattern / 100MHz ~= 100μW / kpattern / MHz
+ plus standard cell logic

AMCHIP04: MAJORITY LOGIC

Pattern match logic is made by identical logic for each layer:
Receives in input 3 bits, if not matching shift down the output.

At the end of the chain the 3 bits are compared with the majority requirements: perfect match, 1 or 2 missing



OR disable match
OR match all patterns
to readout all of them with
matched layers (bitmap)

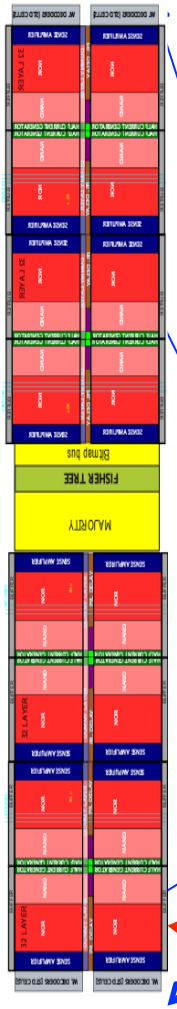
Ready for full-custom, now
syntethized with standard cells

Logic proposed by J. Hoff (Fermilab)

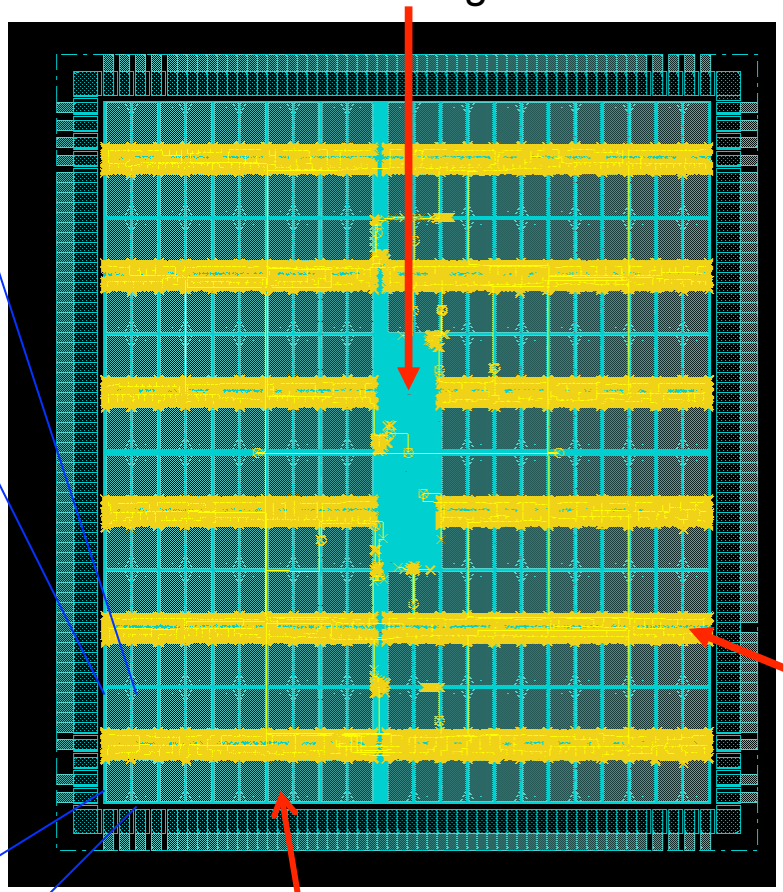
Layer matches from CAM layers are stored in a FF just before resetting the CAM layers.
We can load an event in the CAM layers while we are reading the patterns found in the previous event.

Prototype Chip Layout

64 patterns



Control logic



The AMchip has an area of 14 mm²

CAM is organized as 22 column x 12 row matrix of full custom memory blocks

Each block is 64 x 4 layers

Between two rows of blocks there is the majority logic and the readout logic implemented with standard cells

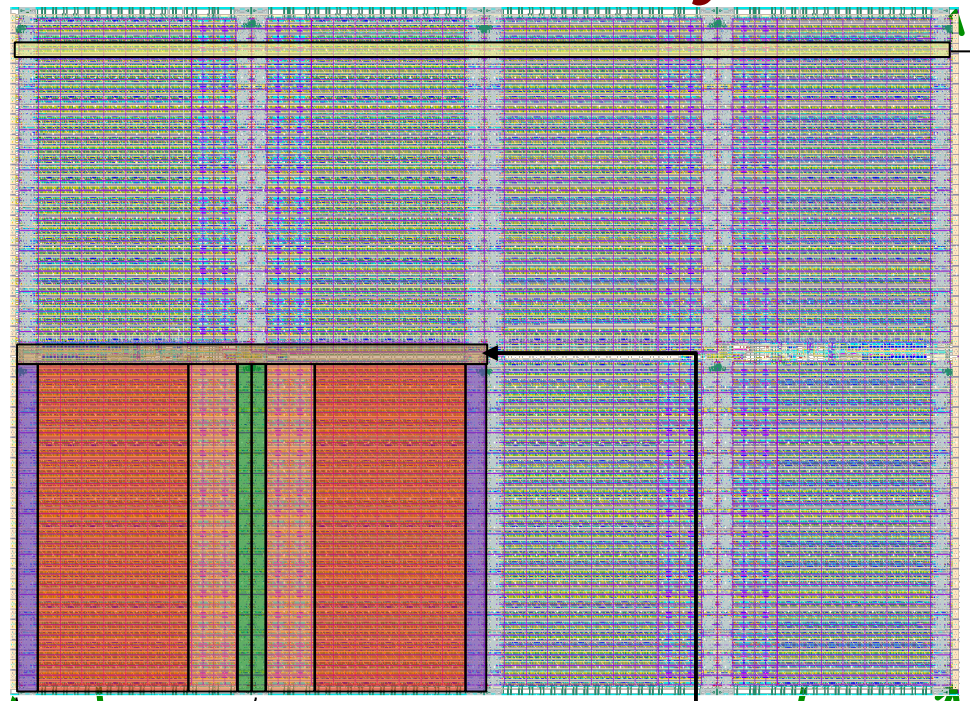
In the center there is the control logic implemented with standard cells

Majority logic and readout logic

size: 3510 μm $\times$ 3985.0 μm

2x128 blocks: 64 half patterns each

Memory Block Layout



4 Layers = 1/2 pattern

Full custom Layout of 64 x 4 CAM layers (half pattern):
w=~226 µm h=~123 µm

without including: majority logic, readout logic, and control logic

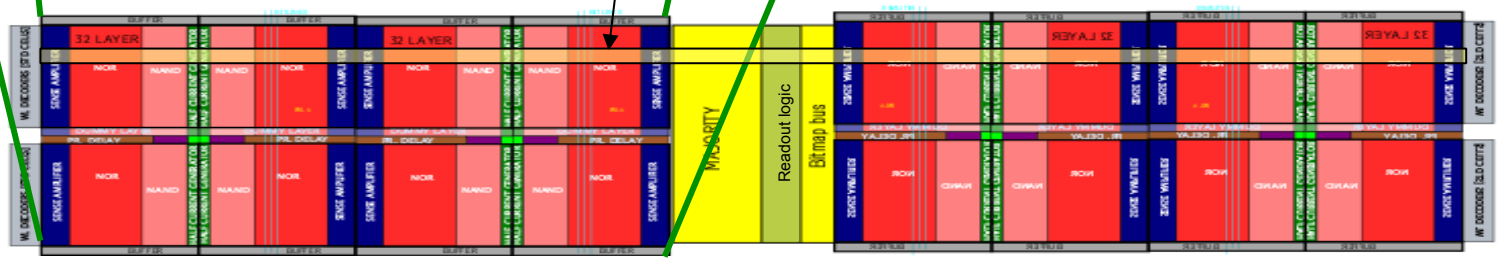
Six metal layers are used to route signals, power supply and ground.

Bit lines are routed vertically while control lines and memory output are routed horizontally

32 CAM layer memory block

Dummy layer

SINGLE PATTERN

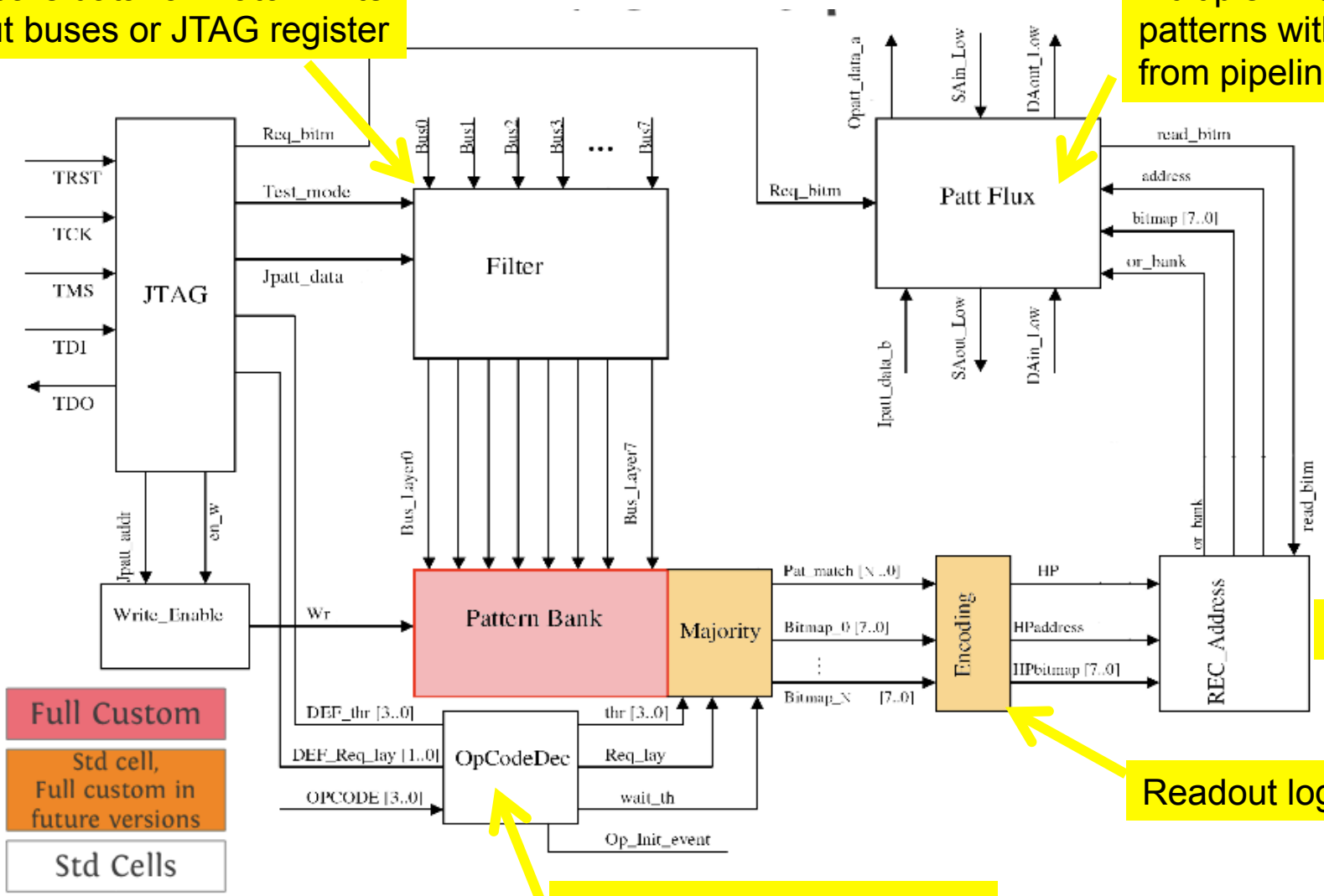


64 patterns (vertically)

AMchip TOP level

Prepare data for match/write
Input buses or JTAG register

Multiplex internal
patterns with those
from pipelined Amchips



register

Readout logic

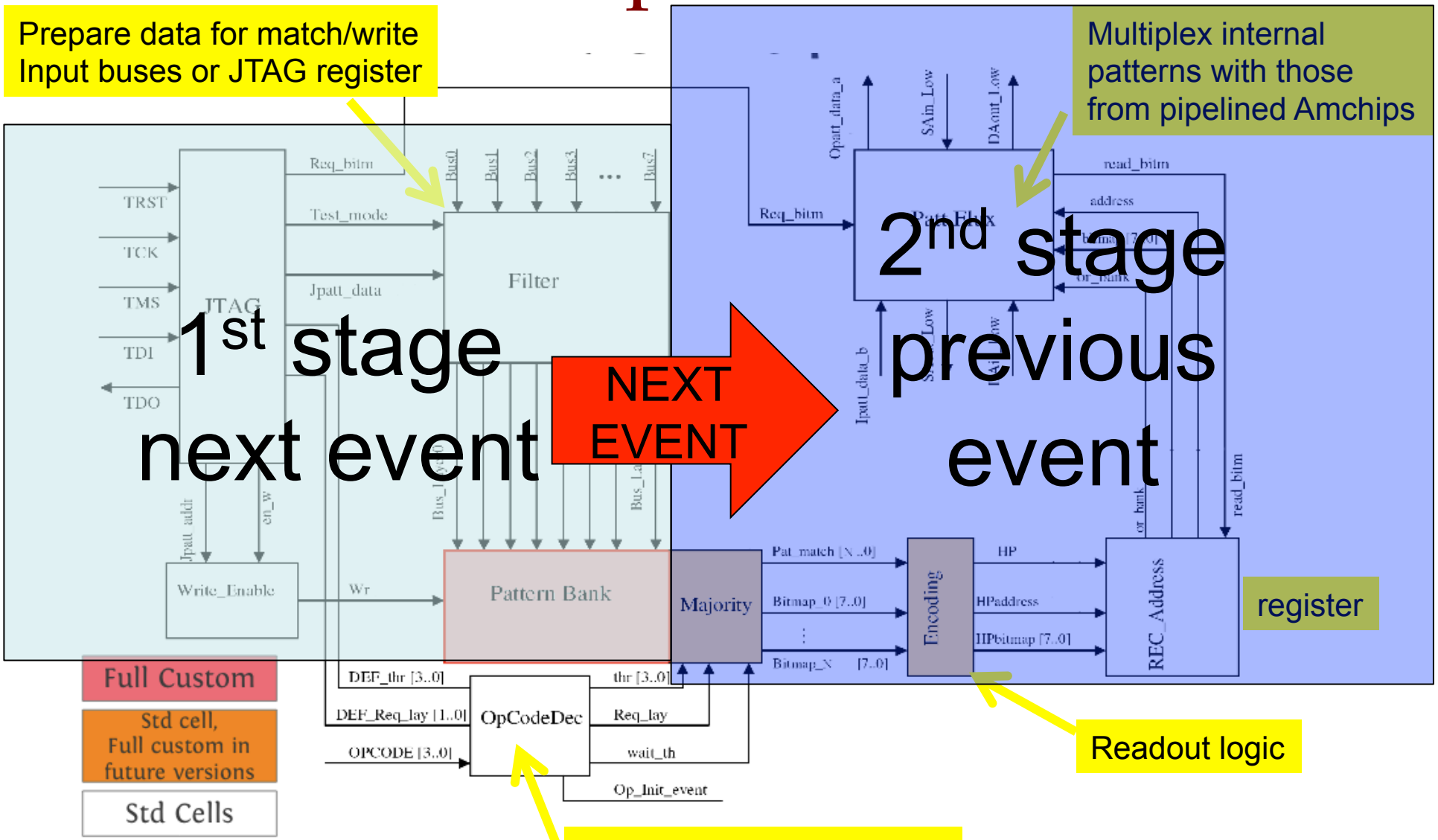
Define matching condition

Full Custom

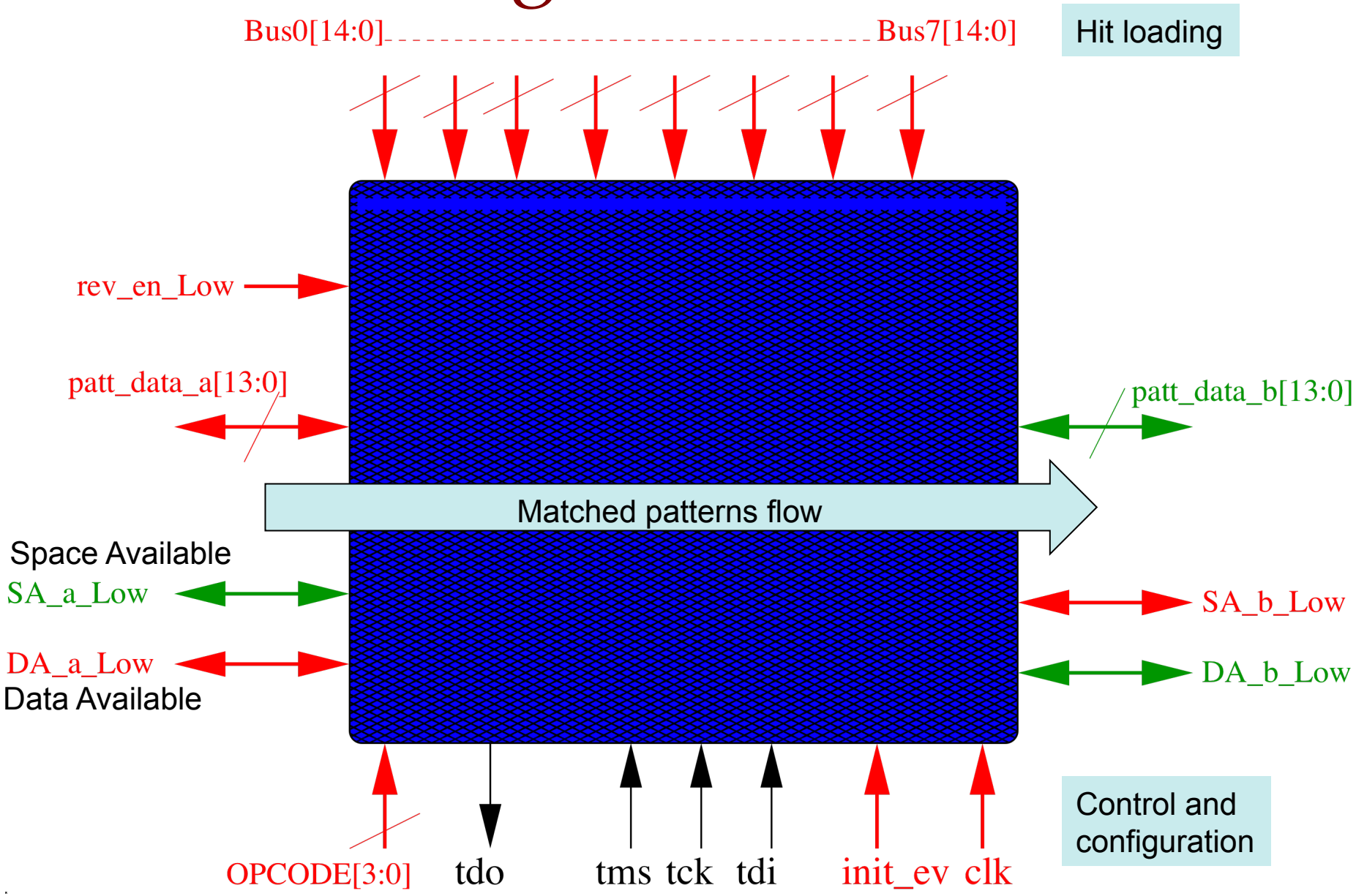
Std cell,
Full custom in
future versions

Std Cells

AMchip TOP level



Logical Pinout



OPCODES

Pattern matching condition changed dynamically with opocdes

code	mnemonic	delay	description
0	NOP	-	Do nothing.
1	SET_0MISS	2	Set the threshold to 0-miss.
2	SET_1MISS	2	Set the threshold to 1-miss.
3	SET_2MISS	2	Set the threshold to 2-miss.
5	INIT_EV	2	1st cycle: reset 2nd stage logic and set THR and required_layers to the default value ("DEF_" registers), copy matched layers to 2nd stage; 2nd cycle reset 1st satge logic
7	DEC_THR	2	Decrease THR register by 1.
10	FORCE_MATCH	2	Set THR to 0 and force all patterns to be readout along with their bitmap.
11	DIS_MATCH	2	Disable the matches.
14	TOGGLE_REQ	2	Enable/disable (toggle) the request of layer0 match
4, 6 8, 9, 12 13,15	reserved	-	

Other applications

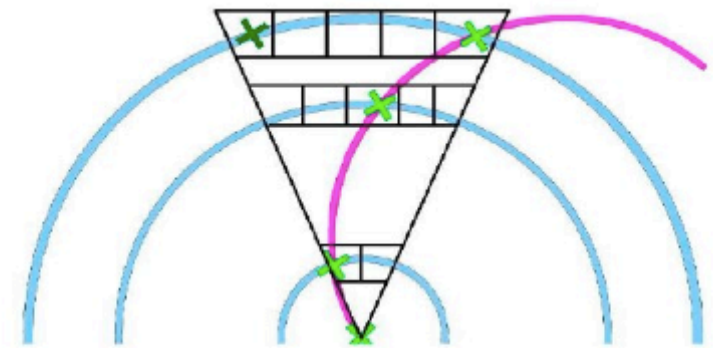
- CMS L1 track trigger
  - First study of Amchip used to trigger with doublets
  - See Thursday G. Boudoul's talk
- ATLAS L1 track trigger
  - Being evaluated
  - See Thursday R. Brenner's talk
- ATLAS Muon upgrade trigger (?)
  - Find micromega muon segments

Summary

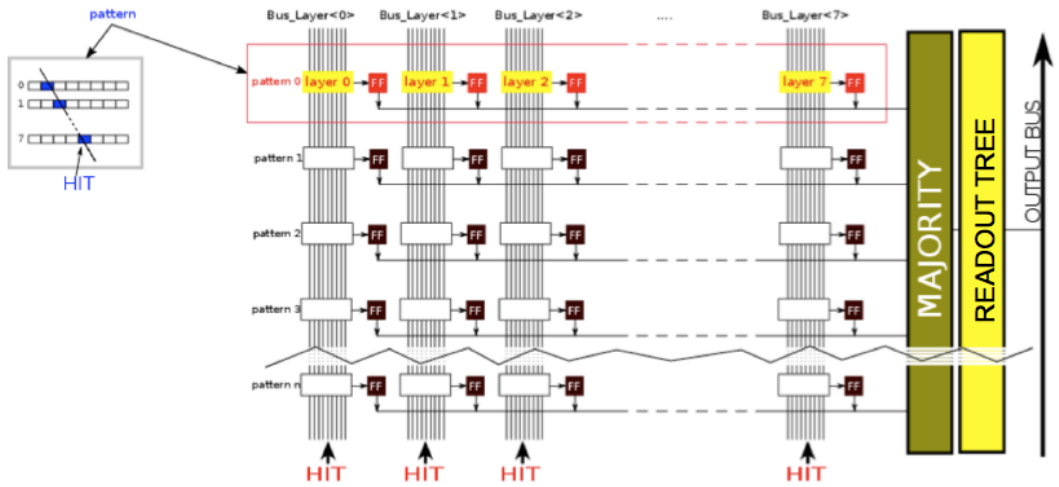
- Designed a new Associative Memory
- First application: ATLAS Fast-Tracker
- Special care to minimize power consumption & increase patt. density
- NEW: introduce powerful variable resolution pattern-matching !!!
  - any coincidence based trigger can profit
  - equivalent to a factor 3-5 extra patterns
- Prototype main goal: verify functionality of new features and full-custom cell
- Expecting delivery of AMchip04 prototype this month

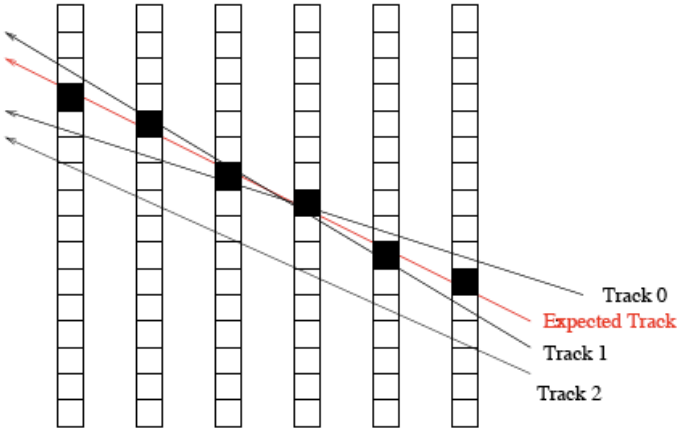
BACKUP

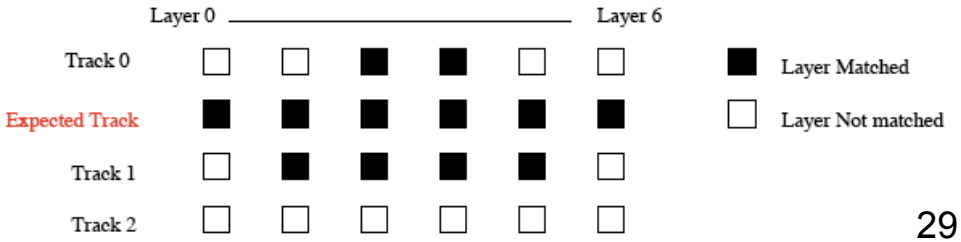
AM working principle



	Lay0	Lay1	Lay2
Template:	01	10	000
Search data:	01	10	000
			100







CAM cell configuration

- 18 CAM bits per layer: 4 NAND and 14 NOR
  - NOR pairs can make a ternary cell
- Default 12 bits + 3 ternary (minimum)
  - 15 bits per input bus (maximum)
  - (14:7) NOR, (6:3) 4 NAND, (2:0) 3 NOR-pairs
- 6 bits + 6 ternary (maximum)
  - Use only 12 bits per input bus
  - (11:10) NOR, (9:6) 4 NAND, (5:0) 6 NOR-pairs
- Ternary cells (NOR pairs) mapped to LSBs
- NAND cells are mapped to LSBs after the ternary cells, when they don't match small power consump.

Ternary CAM Cell with two NOR type cells

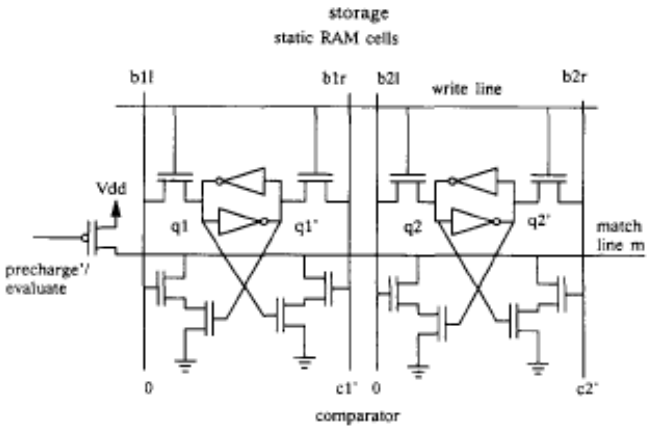


Fig. 8. Two adjacent static binary CAM cells.

storage scheme
stored values

	q1q2
0	01
1	10
*	00

(a)

retrieval scheme
presented values

presented ternary value	encoded value in the bit lines of two binary static CAMS. c1c2	b1l	b1r	b2l	b2r	binary CAM equivalent operation l r
0	01	0	1	0	0	0 M*
1	10	0	0	0	1	M 0
*	11	0	0	0	0	M M

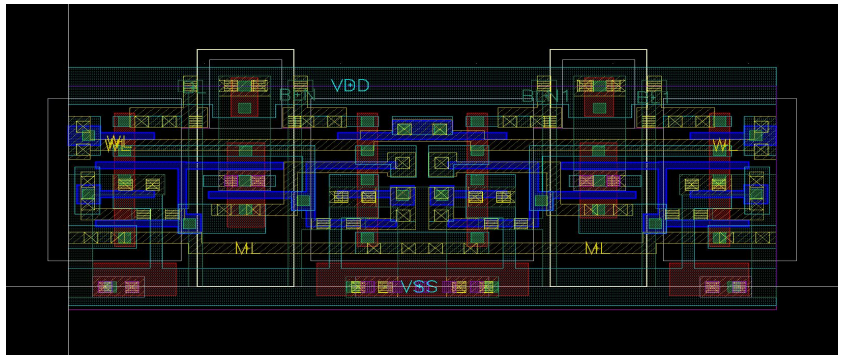
*M is the masking of a bit operation common in commercial binary CAMS.

(b)

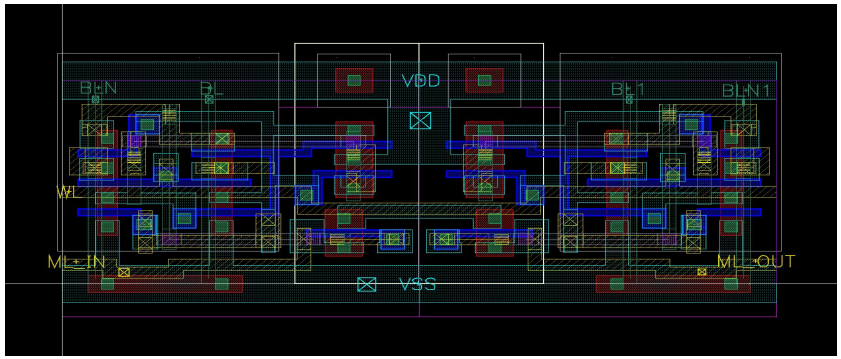
Fig. 9. Encoding and retrieval schemes for don't-care in two static binary CAM's cells with masking capability. (a) Encoding scheme. (b) Retrieval scheme.

Images from: "*Encoding Don't Cares in Static and Dynamic Content-Addressable Memories*", Sergio R. Ramirez-Chavez, IEEE Transactions on circuits and system-II: Analog and Digital Signal Processing, Vol. 39 NO. 8, August 1992

NOR and NAND Cell Layout



Double NOR cell layout
10 transistors each cell
Dimensions: 5.5 X 1.8 μm²



Double NAND cell layout
9 transistors each cell
Dimensions: 5.27 X 1.8 μm²

Layout of memory cells is of type “wide” with uniform orientation of all the transistors in the cells to provide better reproducibility (W and L matching) and transistors V_{th} matching.